

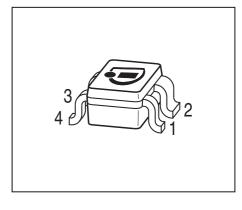
Active Bias Controller

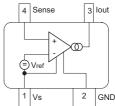
Characteristics

- Supplies stable bias current from 1.8V operating voltage on
- Low voltage drop:
 110mV for 10mA collector currrent

Application notes

- Stabilizing bias current of NPN transistors and FET's from 100µA to 20mA
- Ideal supplement for Sieget and other transistors





- Pb-free (RoHS compliant) package 1)
- Qualified according AEC Q101





Type	Marking	Pin Configuration				Package
BCR410W	W8s	1= Vs	2=GND	3=lout	4=Sense	SOT343

Maximum Ratings

Parameter	Symbol	Value	Unit
Supply voltage	V _S	18	V
Output current	l _{out}	0.5	mA
Total power dissipation, T_S = 110 °C	P _{tot}	100	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stq}	-65 150	

Thermal Resistance

Junction - soldering point ²⁾	R _{thJS}	≤ 470	K/W
carretter coraciming point	1 ' '11135	•	

¹Pb-containing package may be available upon special request

 $^{^2\}mbox{For calculation of}\,\mbox{\it R}_{\mbox{\scriptsize thJA}}$ please refer to Application Note Thermal Resistance



Electrical Characteristics at T_A = 25°C, unless otherwise specified

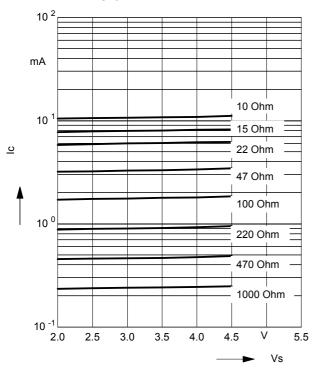
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics	•	•	!	!	•
Additional current consumption	10	-	200	400	μA
V _S = 3 V					
DC Characteristics with stabilized NPN	I-Transistors	•	•	•	•
Lowest sufficient battery voltage	V _{Smin}	-	1.8	-	V
Voltage drop	$V_{ m drop}$	-	110	-	mV
$I_{\rm C}$ = 10 mA					
Change of I _C versus h _{FE}	$\Delta I_{\rm C}/I_{\rm C}$	-	tbd	-	Δh _{FE}
$h_{\sf FE} = 50$					h _{FE}
Change of $I_{\mathbb{C}}$ versus $V_{\mathbb{S}}$	$\Delta I_{\rm C}/I_{\rm C}$	-	2	-	%/V
V _S = 3 V					
Change of $I_{\mathbb{C}}$ versus $T_{\mathbb{A}}$	$\Delta I_{\rm C}/I_{\rm C}$	-	0.15	-	%/K



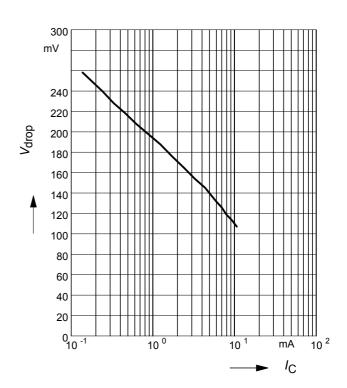
Collector Current $I_C = f(V_S)$

of stabilized NPN Transistor

Parameter $R_{\text{ext.}}(\Omega)$

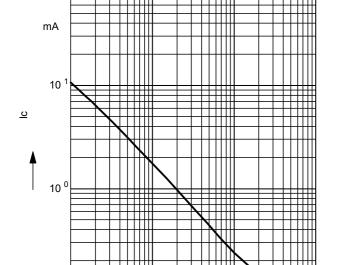


Voltage drop $V_{\text{drop}} = f(I_{\text{C}})$



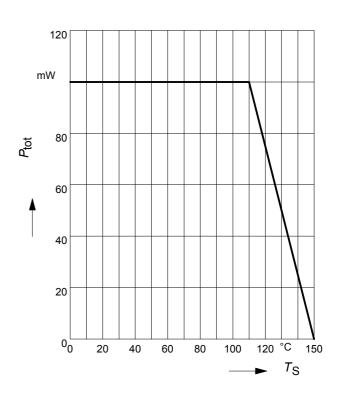
Collector current $I_{C} = f(R_{ext.})$ of stabilized NPN Transistor

10²



10³

Total power dissipation $P_{\text{tot}} = f(T_{\text{S}})$

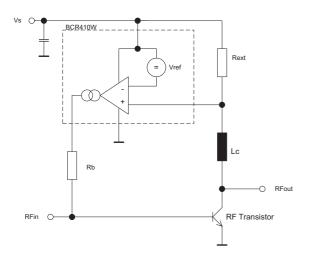


Ohm 10 4

Rext



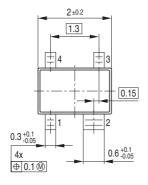
Application Circuit:

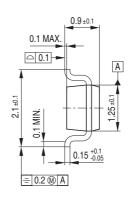




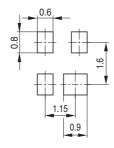
Package Outline



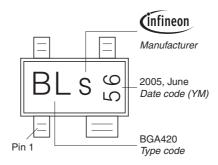




Foot Print

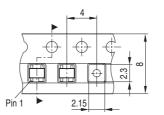


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel







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